

Title (en)

THIN FILM TRANSISTOR, METHOD FOR MANUFACTURING THE SAME, AND DISPLAY

Title (de)

DÜNNFILMTRANSISTOR, VERFAHREN ZU SEINER HERSTELLUNG UND DISPLAY

Title (fr)

TRANSISTOR EN FILM MINCE, PROCÉDÉ DE FABRICATION DE CELUI-CI ET DISPOSITIF D'AFFICHAGE

Publication

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Application

EP 07807228 A 20070913

Priority

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Abstract (en)

Disclosed is a thin film transistor which is characterized by including a gate electrode 3, a gate insulating film 4, a channel layer 5 and source/drain layers 7, 8 stacked over a substrate 2 in this order or in reverse order, wherein the source/drain layers 7, 8 include n-type microcrystalline silicon layers 7a, 8a and n-type amorphous silicon layers 7b, 8b, which are so arranged that the n-type microcrystalline silicon layers 7a, 8a are on the channel layer 5 side. Also disclosed are a method for manufacturing such a thin film transistor and a display.

IPC 8 full level

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